

ABSTRACT OF THE DISCLOSURE

An exposure method for exposing a wafer having magnetic material by using an electron beam, includes: placing the wafer on a wafer stage; calculating a correction value that corrects a deflection amount by a deflector that deflects the electron beam, based on an irradiation position on the wafer, on which the electron beam is to be incident, and a magnetic field formed by the magnetic material; and deflecting the electron beam based on the correction value to expose the wafer.